

Amendments with respect to the Specification:

Page 1 In the crossreferencing space following the Title insert:

This Application is a divisional Application of Parent Application

Serial No.09/703,734 filed 11/1/2000

Page 3 line 2 insert a space between "below" and "through" by inserting the (below through) in parenthesis to replace the underlined belowthrough.

A clean copy of the amended portion of the paragraph on page 3 is as follows:

diffusion barrier film are disposed in thin trenches in an interlevel dielectric material (ILD), connections are made to levels above and below through metal filled vias in the ILD, masking is employed both to protect the dielectric material between conductors during processing operations, and to assist in patterning those trenches within the interlevel dielectric material. A dielectric cap is also usually applied over the surfaces of the metal lines and the masking layer, to further separate successive levels of metal wiring.

Amendments with respect to the Specification - continued.

Page 5 line 5 correct the spelling of "ion" by inserting (ion) in parenthesis to replace the underlined on .

A clean copy of the amended portion of the paragraph on page 5 is as follows:

The materials of which masks are made vary in both reactive ion etch resistance and in dielectric constant and thus present further considerations in fabrication process selection. Acceptable mask materials are amorphous silicon, carbon, hydrogen(~~cc~~-Si:C:H); silicon, carbon, oxygen, hydrogen alloys (organosiloxane or Si:O:H); silicon, nitrogen, carbon alloys (Si:N:C); silicon nitride (Si_3N_4); silicon dioxide (SiO_2); and , silicon oxynitride (SiON).